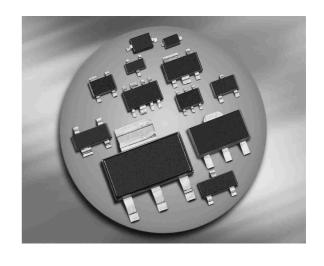


Silicon Schottky Diodes

- For low-loss, fast-recovery, meter protection, bias isolation and clamping application
- Integrated diffused guard ring
- Low forward voltage
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101







BAT64

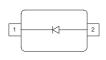
BAT64-02W BAT64-02V

3 D1 D1 D2

BAT64-04

BAT64-05 BAT64-05W BAT64-06 BAT64-06W









ESD (Electrostatic discharge) sensitive device, observe handling precaution!

Туре	Package	Configuration	L _S (nH)	Marking
BAT64	SOT23	single	1.8	63s
BAT64-02V	SC79	single	0.6	t
BAT64-02W*	SCD80	single	0.6	64
BAT64-04	SOT23	series	1.8	64s
BAT64-04W	SOT323	series	1.4	64s
BAT64-05	SOT23	common cathode	1.8	65s
BAT64-05W	SOT323	common cathode	1.4	65s
BAT64-06	SOT23	common anode	1.8	66s
BAT64-06W	SOT323	common anode	1.4	66s

^{*} Not for new design



Maximum Ratings at T_A = 25 °C, unless otherwise specified

Parameter	Symbol	Value	Unit
Diode reverse voltage	V_{R}	40	V
Forward current	I _F	250	mA
Non-repetitive peak surge forward current	I _{FSM}	800	
(<i>t</i> ≤ 10ms)			
Average rectified forward current (50/60Hz, sinus)	I _{FAV}	120	
Total power dissipation	P _{tot}		mW
BAT64, <i>T</i> _S ≤ 86°C		250	
BAT64-02W, -02V $T_{S} \le 121^{\circ}$ C		250	
BAT64-04, BAT64-06, <i>T</i> _S ≤ 61°C		250	
BAT64-04W, BAT64-06W, <i>T</i> _S ≤ 111°C		250	
BAT64-05, <i>T</i> _S ≤ 36°C		250	
BAT64-05W, $T_{S} \le 104^{\circ}\text{C}$		250	
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 150	

Thermal Resistance

Symbol	Value	Unit
R _{thJS}		K/W
	≤ 255	
	≤ 115	
	≤ 355	
	≤ 155	
	≤ 455	
	≤ 185	
		R _{thJS} ≤ 255 ≤ 115 ≤ 355 ≤ 155 ≤ 455

 $^{^{1}}$ For calculation of R_{thJA} please refer to Application Note AN077 (Thermal Resistance Calculation)



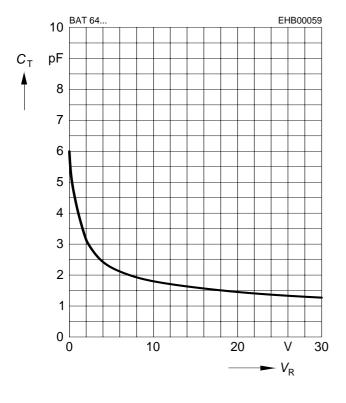
Electrical Characteristics at T_A = 25 °C, unless otherwise specified

Parameter	Symbol		Unit			
		min.	typ.	max.	<u> </u>	
DC Characteristics	•	•	•	•	•	
Breakdown voltage	$V_{(BR)}$	40	-	-	V	
$I_{(BR)} = 10 \ \mu A$						
Reverse current	I_{R}				μA	
V _R = 30 V		-	-	2		
V_{R} = 30 V, T_{A} = 85 °C		-	-	200		
Forward voltage	V _F				mV	
$I_{F} = 1 \; mA$		270	320	350		
$I_{\rm F}$ = 10 mA		310	385	430		
$I_{F} = 30 \text{ mA}$		370	440	520		
$I_{\rm F}$ = 100 mA		500	570	750		
AC Characteristics						
Diode capacitance	C _T	-	4	6	pF	
$V_{R} = 1 \text{ V}, f = 1 \text{ MHz}$						
Reverse recovery time	t _{rr}	-	-	5	ns	
$I_{\rm F}$ = 10 mA, $I_{\rm R}$ = 10 mA, measured $I_{\rm R}$ = 1 mA ,						
R_{L} = 100 Ω						



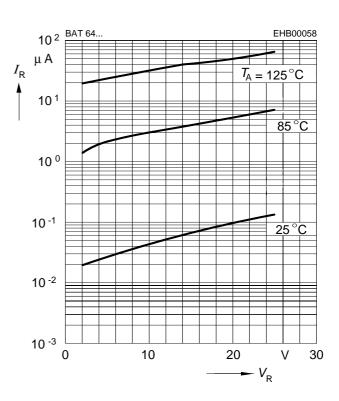
Diode capacitance $C_T = f(V_R)$

f = 1MHz



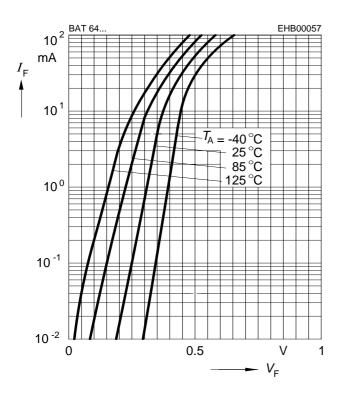
Reverse current $I_R = f(V_R)$

 T_A = Parameter



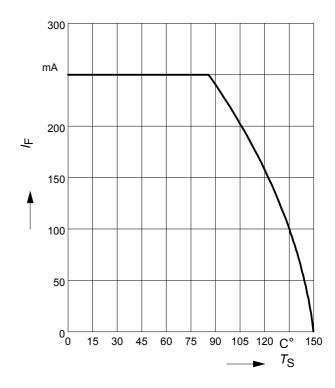
Forward current $I_F = f(V_F)$

 T_A = Parameter



Forward current $I_F = f(T_S)$

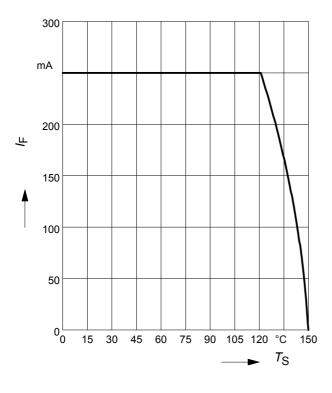
BAT64





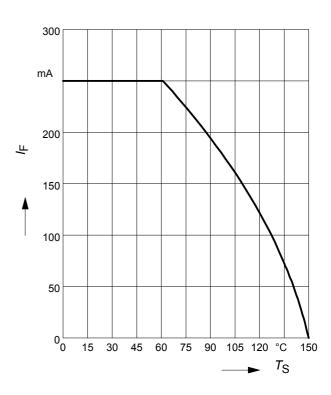
Forward current $I_F = f(T_S)$

BAT64-02W, -02V



Forward current $I_F = f(T_S)$

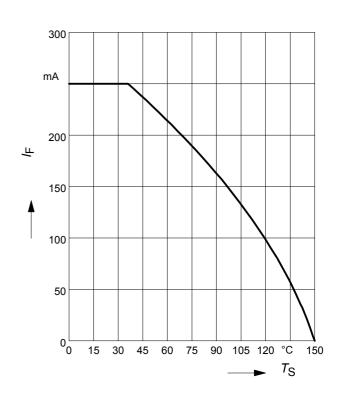
BAT64-04, BAT64-06



Forward current $I_F = f(T_S)$ BAT64-04W, BAT64-06W

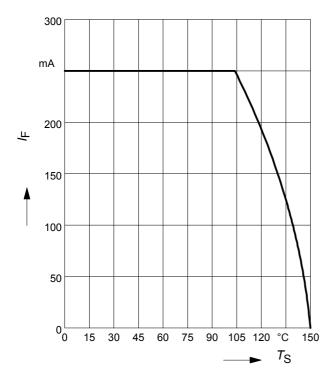
Forward current $I_F = f(T_S)$

BAT64-05

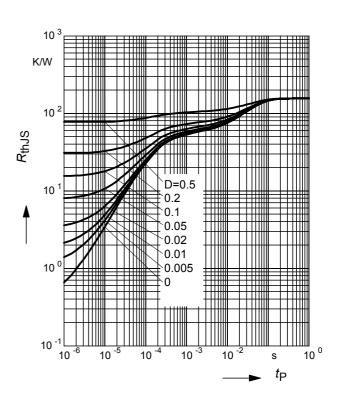




Forward current $I_F = f(T_S)$ BAT64-05W

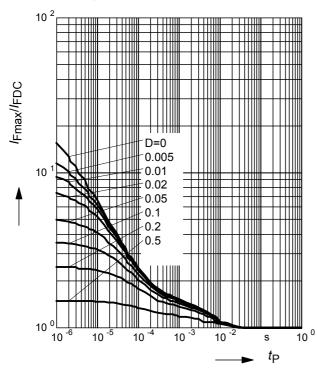


Permissible Puls Load $R_{thJS} = f(t_p)$ BAT64-02W, -02V



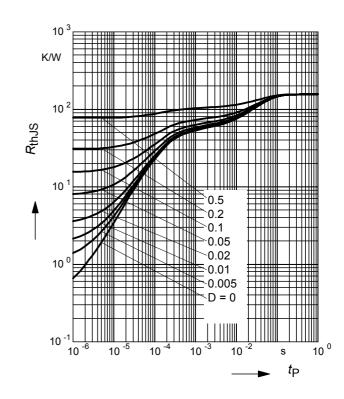
Permissible Pulse Load

 $I_{\text{Fmax}}/I_{\text{FDC}} = f(t_{\text{p}})$ BAT64-02W, -02V



Permissible Puls Load R_{thJS} = $f(t_p)$

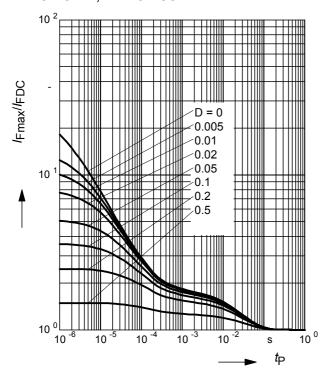
BAT64-04W, BAT64-06W



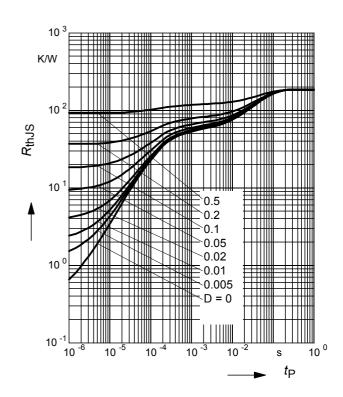


Permissible Pulse Load

 $I_{\text{Fmax}} / I_{\text{FDC}} = f (t_{\text{p}})$ BAT64-04W, BAT64-06W

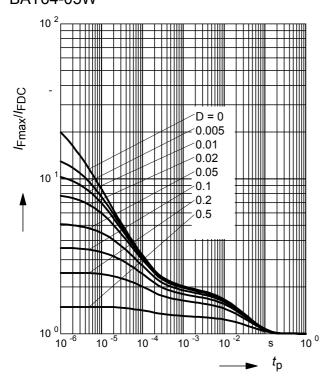


Permissible Puls Load $R_{thJS} = f(t_p)$ BAT64-05W

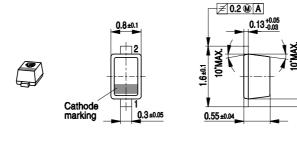


Permissible Pulse Load

 $I_{\text{Fmax}}/I_{\text{FDC}} = f(t_{\text{p}})$ BAT64-05W



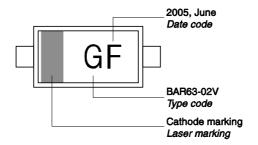




Foot Print



Marking Layout (Example)

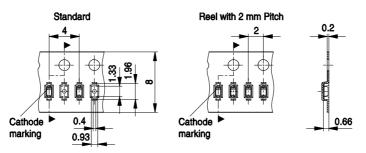


Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel

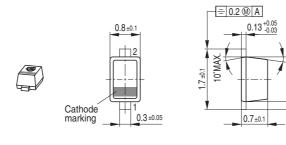
Reel ø180 mm = 8.000 Pieces/Reel (2 mm Pitch)

Reel ø330 mm = 10.000 Pieces/Reel



8

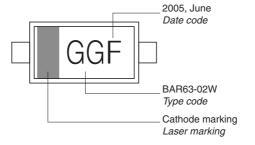




Foot Print



Marking Layout (Example)

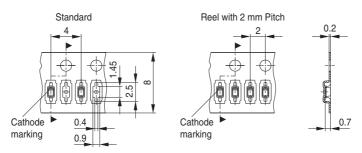


Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel

Reel ø180 mm = 8.000 Pieces/Reel (2 mm Pitch)

Reel ø330 mm = 10.000 Pieces/Reel



9

2014-02-11



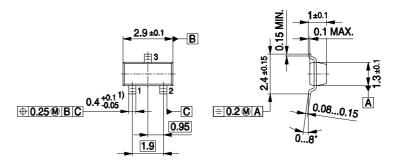
Date Code marking for discrete packages with one digit (SCD80, SC79, SC75¹⁾) CES-Code

Month	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012	2013	2014
01	а	р	Α	Р	а	р	Α	Р	а	р	Α	Р
02	b	q	В	Q	b	q	В	Q	b	q	В	Q
03	С	r	С	R	С	r	С	R	С	r	С	R
04	d	S	D	S	d	S	D	S	d	S	D	S
05	е	t	Е	T	е	t	Е	Т	е	t	Е	Т
06	f	u	F	U	f	u	F	U	f	u	F	U
07	g	٧	G	V	g	٧	G	٧	g	٧	G	V
08	h	Х	Η	Х	h	Х	Н	Х	h	Х	Η	Х
09	j	у	7	Υ	j	у	J	Υ	j	у	7	Υ
10	k	Z	K	Z	k	Z	K	Z	k	Z	K	Z
11	I	2	L	4	I	2	L	4	I	2	L	4
12	n	3	N	5	n	3	N	5	n	3	N	5

¹⁾ New Marking Layout for SC75, implemented at October 2005.



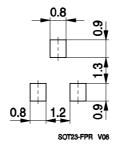




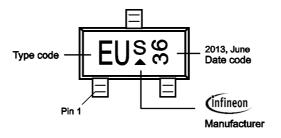
1) Lead width can be 0.6 max. in dambar area

SOT23-PO V08

Foot Print

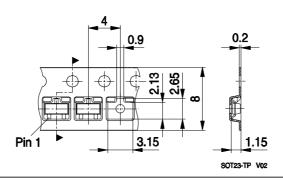


Marking Layout



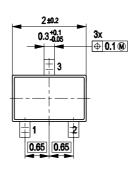
Standard Packing

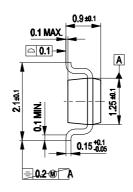
Reel o 180 mm: 3.000 Pieces / Reel Reel o 330 mm = 10.000 Pieces / Reel



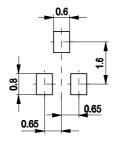




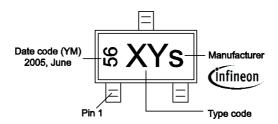




Foot Print

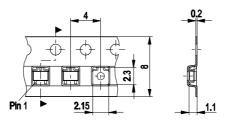


Marking Layout (Example)



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel Reel ø330 mm = 10.000 Pieces/Reel





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